

# LED CHIP C970-40

## SPECIFICATION OF LED CHIP C970-40 [INFRARED]

### 1) Commodity Type and Physical Characteristics.

- |                      |             |                             |
|----------------------|-------------|-----------------------------|
| 1. Material          | GaAs/GaAs   |                             |
| 2. Electrode         | Top Side    | P (anode) side : Au Alloy   |
|                      | Bottom Side | N (cathode) side : Au Alloy |
| 3. Electrode Pattern | Fig.1       |                             |
| 4. Chip Size         | Fig.2       |                             |
| 5. Chip Thickness    | Fig.2       |                             |
| 6. Emission Area     | Fig.2       |                             |

### 2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.25	1.35	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	0.5	1.0		mW
Peak Wavelength	λ P	If=20mA	960	970	980	nm
Spectral Radiation Bandwidth	DI	If=20mA		50		nm
RiseTime	tr	If=20mA		1000		ns
FallTime	tf	If=20mA		500		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : um]

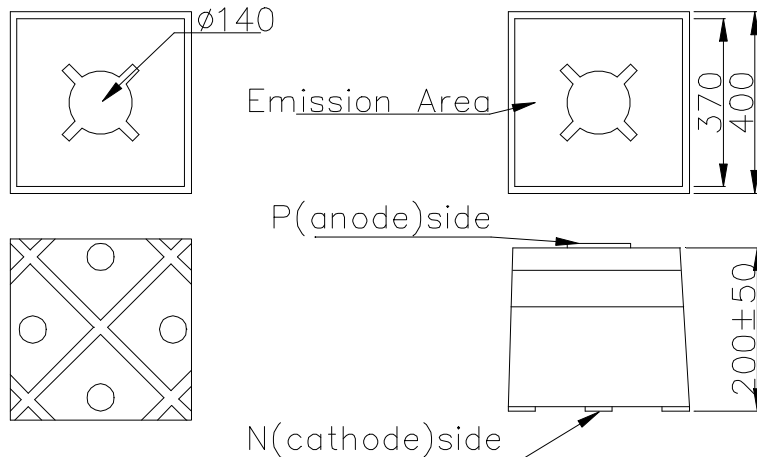


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area